

# isc N-Channel Mosfet Transistor

## BUZ202

### • FEATURES

- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 0.5 \Omega$  (Max)
- SOA is Power Dissipation Limited
- High input impedance
- High speed switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • DESCRIPTION

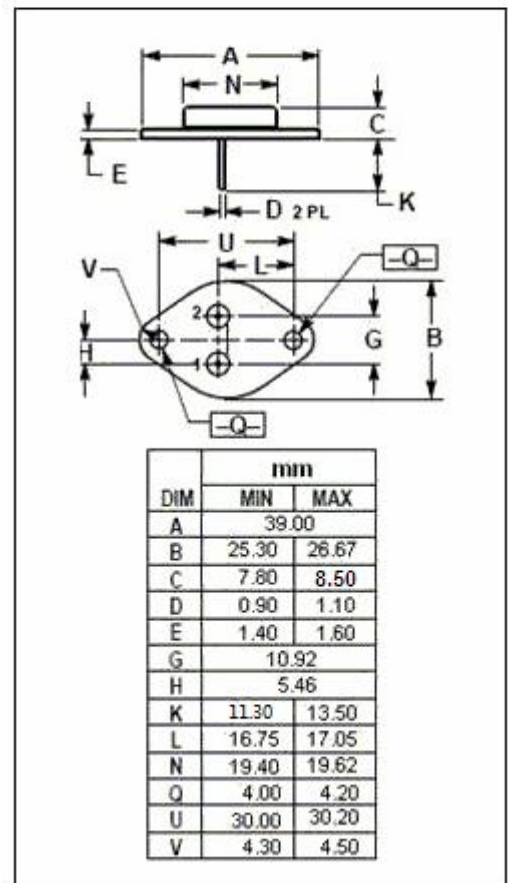
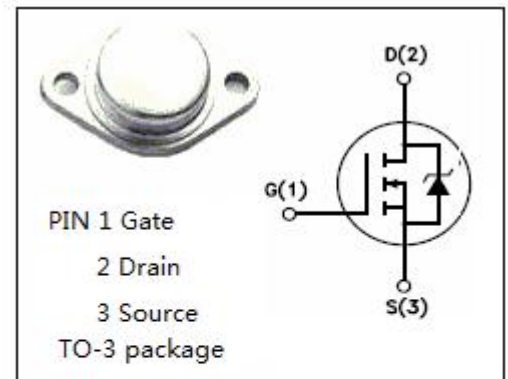
Designed for applications such as switching regulators, switching converters, motor drivers, relay drivers and drivers for high power bipolar switching transistors requiring high speed and low gate drive power .

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	400	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $TC=25^\circ\text{C}$	11.5	A
$I_{DM}$	Drain Current-Single Pulsed	46	A
$P_{tot}$	Total Dissipation@ $TC=25^\circ\text{C}$	125	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1	$^\circ\text{C}/\text{W}$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	35	$^\circ\text{C}/\text{W}$



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## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> =0.25mA	400			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.1		4.0	V
V <sub>SD</sub>	Diode Forward On-voltage	I <sub>S</sub> = 23A; V <sub>GS</sub> = 0			1.9	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 8A			0.5	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =400V; V <sub>GS</sub> = 0			250	μA
G <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> = 25V; I <sub>D</sub> =8A	3.3			S
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> =10V; I <sub>D</sub> =2.9A; V <sub>DD</sub> =30V; R <sub>GS</sub> =50 Ω			75	ns
t <sub>r</sub>	Rise Time				120	
t <sub>d(off)</sub>	Turn-off Delay Time				430	
t <sub>f</sub>	Fall Time				140	

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